



BR SERIES

2 to 10kV, 250 to 1000mA, 75nS to Standard Recovery
Axial Lead Power Diodes



Features

- Medium Current
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

Specifications¹

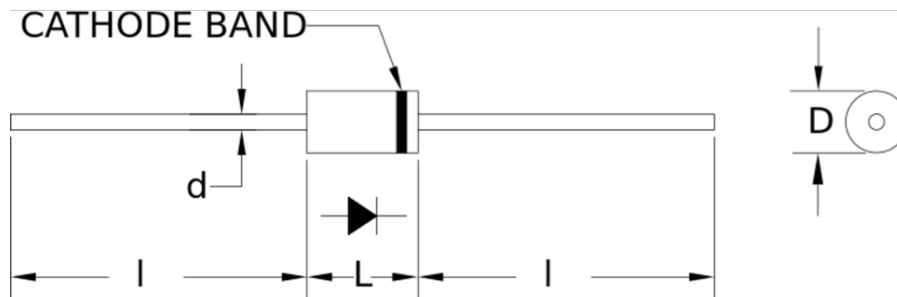
Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} ² nS	L in.	D in.	d in.	l in.
BR2	2000	1000	2.4	5	40	-	-	0.354	0.197	0.05	0.94
BR2F	2000	900	3.8	5	20	35	100	0.354	0.197	0.05	0.94
BR3F	3000	900	3.8	5	40	35	100	0.354	0.197	0.05	0.94
BR4	4000	850	4.4	5	20	-	-	0.354	0.197	0.05	0.94
BR4F	4000	600	7.0	5	20	36	100	0.354	0.197	0.05	0.94
BR5	5000	750	6.0	5	20	-	-	0.354	0.197	0.05	0.94
BR5F	5000	600	8.8	5	20	20	100	0.354	0.197	0.05	0.94
BR6F	6000	500	10.5	5	20	19	100	0.354	0.197	0.05	0.94
BR8F	8000	400	12.9	5	20	14	100	0.354	0.197	0.05	0.94
BR10F	10000	250	14.0	5	40	10	100	0.354	0.197	0.05	0.94
BRU10SF	10000	250	17.0	5	20	7	75	0.354	0.197	0.05	0.94

Temperature °C	
Storage Temperature	-55 to 175
Operating Temperature	-55 to 150
Maximum Junction Temperature	150

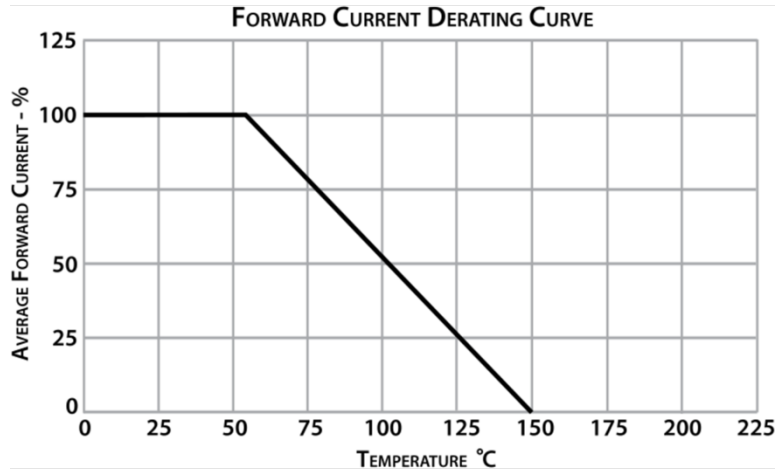
¹25°C ambient temperature unless stated otherwise.

²A "-" indicates that the component is a standard recovery device and no T_{RR} data is taken.

Drawings



Dimensions in inches, tolerances ±0.020 except as noted



Specification Definitions

	Specifications	Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At I _{FAVM}
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3 mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 0.5 I _{FAVM} ; I _R = -I _{FAVM} ; I _{RR} = -0.25 I _{FAVM}

Note: Specifications subject to change without notice. Photo is representation only.

